

Features

- Split Gate Trench MOSFET Technology
- AEC-Q101 Qualified
- · Moisture Sensitivity Level 1
- Extremely Low Switching Loss
- Fast Switching and Soft Recovery
- Halogen Free Available Upon Request By Adding Suffix "-HF"
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

Maximum Ratings

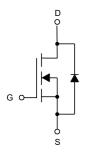
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 1.7°C/W Junction to Case (Steady-State)
- Thermal Resistance: 20°C/W Junction to Ambient (t≤10s)⁽¹⁾
- Thermal Resistance: 50°C/W Junction to Ambient (Steady-State)⁽¹⁾

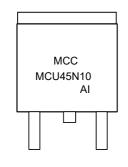
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	100	V
Gate-Source Volltage	V_{GS}	±20	V
Continuous Drain Current	I _D	45	Α
Pulsed Drain Current ⁽²⁾	I _{DM}	180	Α
Total Power Dissipation ⁽³⁾	P _D	72	W
Single Pulsed Avalanche Energy ⁽⁴⁾	E _{AS}	81	mJ

Note:

- 1. The value of $R_{\Theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The Power dissipation P_{DSM} is based on $R_{\Theta JA}$ t≤10s and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.
- 2. Repetitive rating; pulse width limited by max. junction temperature.
- 3. P_D is based on max. junction temperature, using junction-case thermal resistance.
- 4. V_{DD} =50V, R_{G} =25 Ω , L=0.5mH, I_{AS} =18A.

±bh/fbU `Ghfi WhifY`UbX`A Uf_]b['7cXY

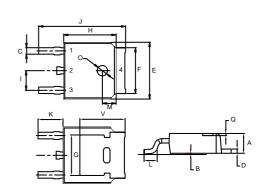




AI: 2 codes in total A is the year I is the month

N-CHANNEL MOSFET

DPAK(TO-252)



- 1. Gate
- 2.4. Drain
 - 3. Source

DIMENSIONS					
DIM	DIM INCHES		MM		NOTE
DIIVI	MIN	MAX	MIN	MAX	NOTE
Α	0.087	0.094	2.20	2.40	
В	0.000	0.005	0.00	0.13	
С	0.026	0.034	0.66	0.86	
D	0.018	0.023	0.46	0.58	
Е	0.256	0.264	6.50	6.70	
F	0.201	0.215	5.10	5.46	
G	0.190		4.83		TYP.
Н	0.236	0.244	6.00	6.20	
ı	0.086	0.094	2.18	2.39	
J	0.386	0.409	9.80	10.40	
K	0.1	14	2.9	90	TYP.
L	0.055	0.067	1.40	1.70	
M	0.0	63	1.6	06	TYP.
0	0.043	0.051	1.10	1.30	
Q	0.000	0.012	0.00	0.30	
V	V 0.211		5.3	35	TYP.

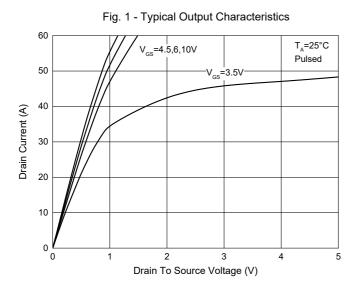


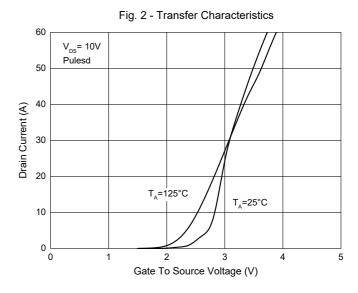
Electrical Characteristics @ 25°C (Unless Otherwise Specified)

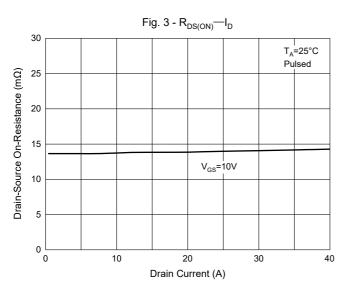
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static Characteristics	1					-	
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250μA	100			V	
Gate-Source Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V			1	μA	
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	1	1.8	2.5	V	
Drain-Source On-Resistance	Б	V _{GS} =10V, I _D =20A		14	17	mΩ	
	R _{DS(on)}	V _{GS} =4.5V, I _D =20A		17	21.5	mΩ	
Gate Resistance	R _g	f=1MHz, Open drain		1		Ω	
Diode Characteristics							
Continuous Body Diode Current	Is				40	Α	
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =20A			1.3	V	
Reverse Recovery Time	t _{rr}	1 004 11 / 11 4004 /		39.8		ns	
Reverse Recovery Charge	Q _{rr}	I _S =20A, dI _F /dt=100A/μs		42		nC	
Dynamic Characteristics							
Input Capacitance	C _{iss}			1135			
Output Capacitance	C _{oss}	V _{DS} =50V,V _{GS} =0V,f=1MHz		399		pF	
Reverse Transfer Capacitance	C _{rss}			18		1	
Total Gate Charge	Q_g			16			
Gate-Source Charge	Q _{gs}	V _{DS} =50V,V _{GS} =10V,I _D =25A		5.6		nC	
Gate-Drain Charge	Q_{gd}			2.4			
Turn-On Delay Time	t _{d(on)}			39.2			
Turn-On Rise Time	t _r	V _{GS} =10V, V _{DD} =50V,I _D =25A		11		no	
Turn-Off Delay Time	t _{d(off)}	R_{GEN} =2.2 Ω		53.2		ns	
Turn-Off Fall Time	t _f			15.8			

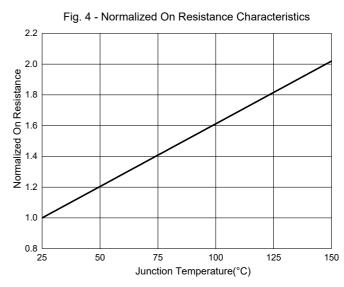


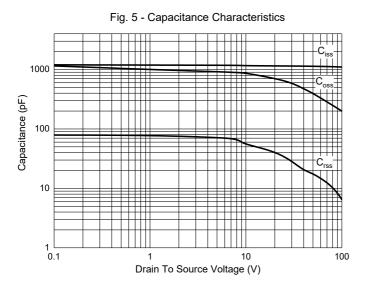
Curve Characteristics

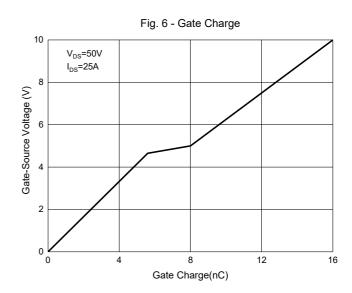






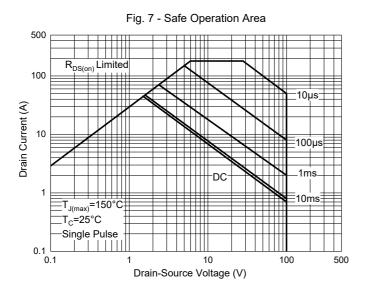


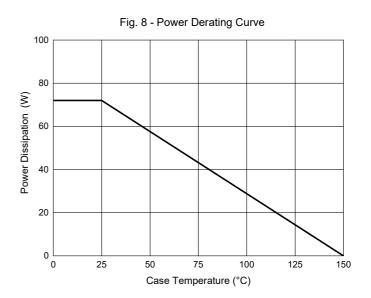


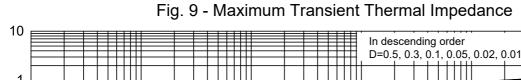


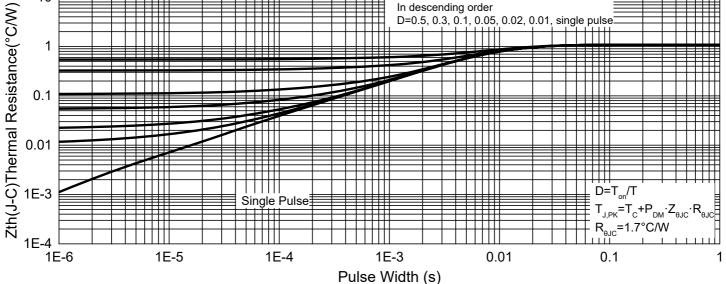


Curve Characteristics









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Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 2.5Kpcs/Reel

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